

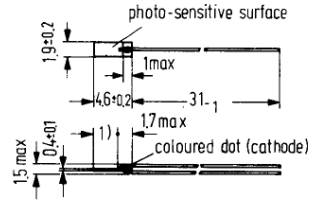
Silicon photo-voltaic cell

The silicon photo-voltaic cell BP 100 is suitable for use in control and regulating devices. Its high response sensitivity, its small dimensions, and the high permissible operating temperature favour universal application.

Since a case can be dispensed with, the cell lends itself to the assembly of high-efficiency scanning systems. For this purpose the cells may be glued closely together on suitable supports. The photo-insensitive side of the element is marked by a yellow dot.

Typ	Order number
BP 100	Q 60215-X100

See mounting instructions



1) contact surface 2.7 mm
Weight approx. 0.2 g Dimensions in mm

Maximum ratings

Reverse voltage¹⁾
Ambient temperature

	BP 100	
V_R	1	V
T_{amb}	- 25 to + 100	°C

Characteristics ($T_{amb} = 25^\circ\text{C}$)

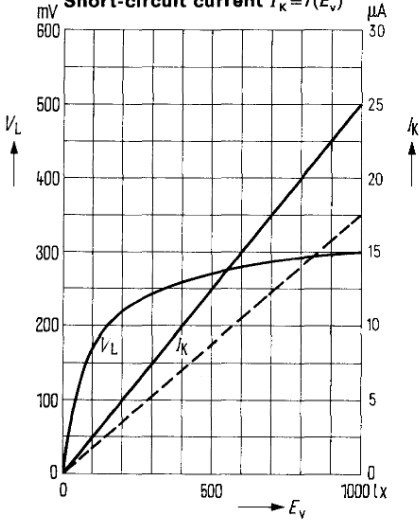
Open-circuit voltage ($E_V = 100 \text{ lx}$)²⁾
 Open-circuit voltage ($E_V = 1000 \text{ lx}$)²⁾
 Short-circuit current ($E_V = 1000 \text{ lx}$)²⁾
 Photo sensitivity (short circuit current I_K)²⁾
 Spectral sensitivity maximum
 Rise time (for 60% I_K)
 Temp. coeff. of the open-circuit voltage
 Temp. coeff. of the short-circuit current
 Capacitance ($V_R = 0 \text{ V}$)
 Light sensitive area
 Dark current ($V_R = 1 \text{ V}$; $T_{amb} = 25^\circ\text{C}$; $E_V = 0 \text{ lx}$)
 Dark current ($V_R = 1 \text{ V}$; $T_{amb} = 50^\circ\text{C}$; $E_V = 0 \text{ lx}$)

V_L	≥ 120	mV
V_L	≥ 200	mV
I_K	25	μA
S	25 (≥ 15)	nA/lx
λ_{smax}	0.85	μm
t_r	4	μs
TC	- 2.6	mV/K
TC	0.121	%/K
C_o	1	nf
A	7	mm ²
I_R	3 (≤ 10)	μA
I_R	7	μA

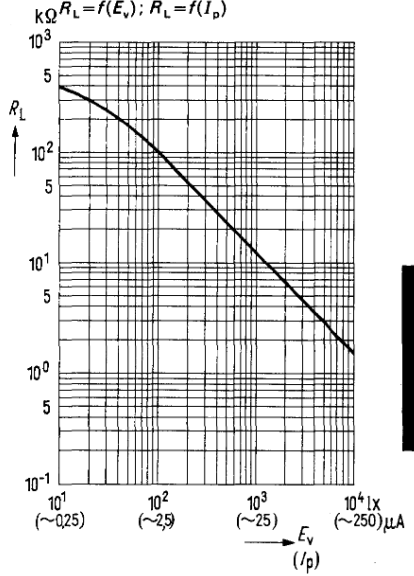
¹⁾ Plus pole of voltage source connected to lead on the colour dot side.

²⁾ The illuminances indicated refers to a radiation source with standard light A acc. to DIN 5033, tungsten filament lamp, colour temperature $T_F = 2856 \text{ K}$ (unfiltered incandescent lamp light).

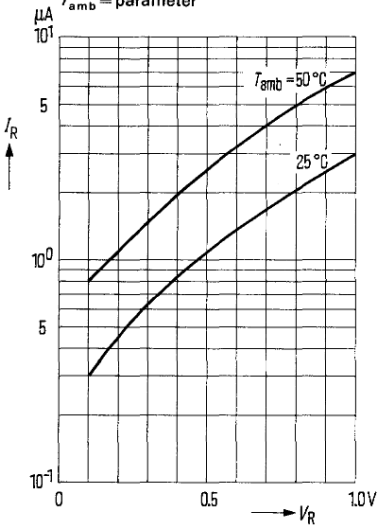
Open-circuit voltage $V_L = f(E_v)$
Short-circuit current $I_k = f(E_v)$



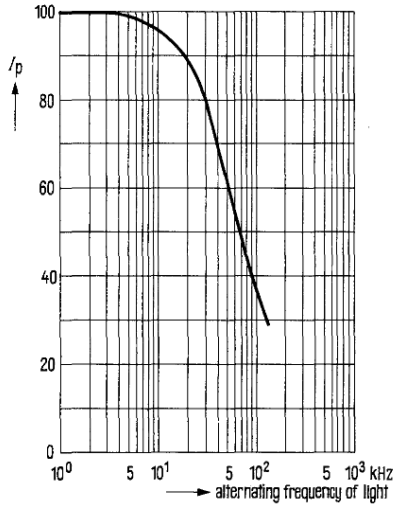
Matching impedance resistor for optimal power output
 $R_L = f(E_v); R_L = f(I_p)$



Dark current $I_R = f(V_R)$
 T_{amb} = parameter



Mean photo current as a function of the light alternating frequency $R_L = 1$ k Ω ; $E_v = 1000$ lx



Directional characteristic $I_K = f(\varphi)$

